

FEATURES

- Low $V_{CE(sat)}$ Device
- 10 μ s Short Circuit Withstand
- High Thermal Cycling Capability
- High Current Density Enhanced DMOS SPT
- Isolated AISiC Base with AlN Substrates
- Lead Free Construction

APPLICATIONS

- High Reliability Inverters
- Motor Controllers
- Traction Auxiliaries
- Choppers

The Powerline range of high power modules includes half bridge, chopper, dual, single and bi-directional switch configurations covering voltages from 1200V to 6500V and currents up to 2400A.

The DIM125PHM33-TL000 is a Low $V_{CE(sat)}$ half bridge 3300V, soft punch through n-channel enhancement mode, insulated gate bipolar transistor (IGBT) module. The IGBT has a wide reverse bias safe operating area (RBSOA). This device is optimised for traction drives and other applications requiring high thermal cycling capability.

The module incorporates an electrically isolated base plate and low inductance construction enabling circuit designers to optimise circuit layouts and utilise grounded heat sinks for safety.

ORDERING INFORMATION

Order As:

DIM125PHM33-TL000

Note: When ordering, please use the complete part number

KEY PARAMETERS

V_{CES}	3300V
$V_{CE(sat)}$ * (typ)	2.0V
I_C (max)	125A
$I_{C(PK)}$ (max)	250A

* Measured at the auxiliary terminals

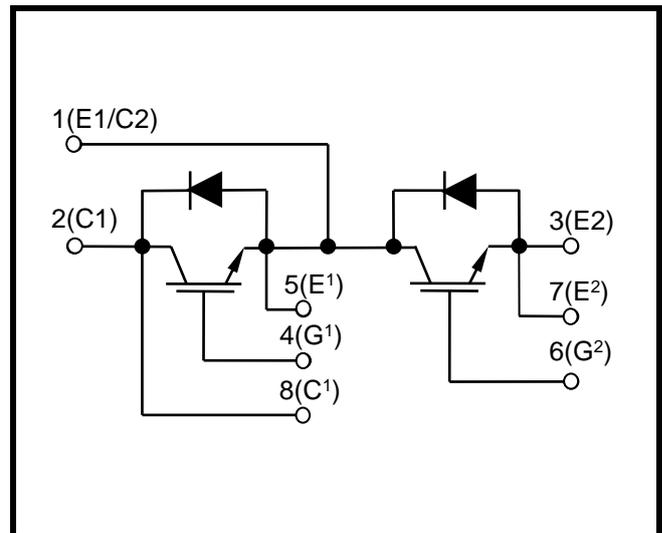
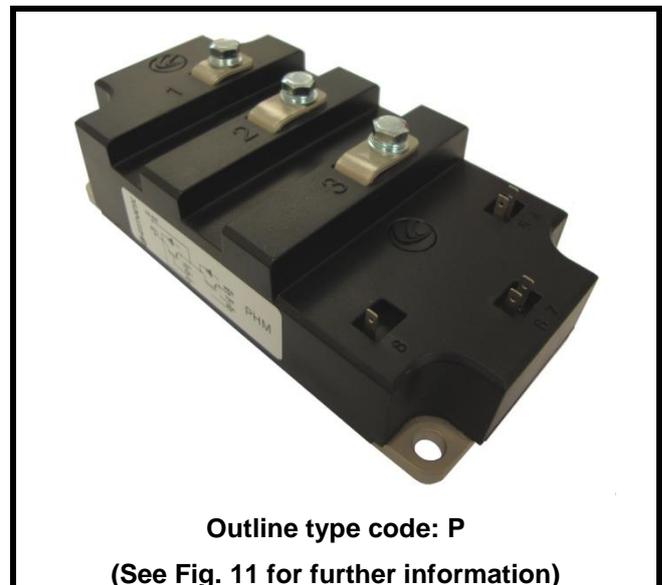


Fig. 1 Circuit configuration



Outline type code: P
(See Fig. 11 for further information)

Fig. 2 Package

ABSOLUTE MAXIMUM RATINGS

Stresses above those listed under ‘Absolute Maximum Ratings’ may cause permanent damage to the device. In extreme conditions, as with all semiconductors, this may include potentially hazardous rupture of the package. Appropriate safety precautions should always be followed. Exposure to Absolute Maximum Ratings may affect device reliability.

T_{case} = 25°C unless stated otherwise

Symbol	Parameter	Test Conditions	Max.	Units
V _{CES}	Collector-emitter voltage	V _{GE} = 0V	3300	V
V _{GES}	Gate-emitter voltage		±20	V
I _C	Continuous collector current	T _{case} = 115°C	125	A
I _{C(PK)}	Peak collector current	1ms, T _{case} = 140°C	250	A
P _{max}	Max. transistor power dissipation	T _{case} = 25°C, T _j = 150°C	1.3	kW
I ² t	Diode I ² t value	V _R = 0, t _p = 10ms, T _j = 125°C	5	kA ² s
V _{isol}	Isolation voltage – per module	Commoned terminals to base plate. AC RMS, 1 min, 50Hz	6000	V
Q _{PD}	Partial discharge – per module	IEC1287, V ₁ = 3500V, V ₂ = 2600V, 50Hz RMS	10	pC

THERMAL AND MECHANICAL RATINGS

Internal insulation material:	AlN
Baseplate material:	AlSiC
Creepage distance:	33mm
Clearance:	20mm
CTI (Comparative Tracking Index):	>600

Symbol	Parameter	Test Conditions	Min	Typ.	Max	Units
R _{th(j-c)}	Thermal resistance – transistor	Continuous dissipation - junction to case	-	-	96	°C/kW
R _{th(j-c)}	Thermal resistance – Diode	Continuous dissipation - junction to case	-	-	192	°C/kW
R _{th(c-h)}	Thermal resistance – case to heatsink (per module)	Mounting torque 5Nm (with mounting grease)	-	-	16	°C/kW
T _j	Junction temperature	Transistor	-	-	150	°C
		Diode	-	-	150	°C
T _{stg}	Storage temperature range	-	-40	-	125	°C
	Screw torque	Mounting – M6	-	-	5	Nm
		Electrical connections – M5	-	-	4	Nm

ELECTRICAL CHARACTERISTICS

$T_{case} = 25^{\circ}C$ unless stated otherwise.

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
I _{CES}	Collector cut-off current	V _{GE} = 0V, V _{CE} = V _{CES}			1	mA
		V _{GE} = 0V, V _{CE} = V _{CES} , T _{case} = 125°C			7.5	mA
		V _{GE} = 0V, V _{CE} = V _{CES} , T _{case} = 150°C			12.5	mA
I _{GES}	Gate leakage current	V _{GE} = ± 20V, V _{CE} = 0V			1	μA
V _{GE(TH)}	Gate threshold voltage	I _C = 10mA, V _{GE} = V _{CE}		5.7		V
V _{CE(sat)}	Collector-emitter saturation voltage	V _{GE} = 15V, I _C = 125A		2.0		V
		V _{GE} = 15V, I _C = 125A, T _j = 125°C		2.6		V
		V _{GE} = 15V, I _C = 125A, T _j = 150°C		2.8		V
I _F	Diode forward current	DC		125		A
I _{FM}	Diode maximum forward current	t _p = 1ms		250		A
V _F	Diode forward voltage	I _F = 125A		2.4		V
		I _F = 125A, T _j = 125°C		2.5		V
		I _F = 125A, T _j = 150°C		2.4		V
C _{ies}	Input capacitance	V _{CE} = 25V, V _{GE} = 0V, f = 1MHz		22.5		nF
Q _g	Gate charge	±15V Including external C _{ge}		2.5		μC
C _{res}	Reverse transfer capacitance	V _{CE} = 25V, V _{GE} = 0V, f = 1MHz		0.5		nF
L _M	Module inductance			40		nH
R _{INT}	Internal transistor resistance			500		μΩ
SC _{Data}	Short circuit current, I _{SC}	T _j = 150°C, V _{CC} = 2500V t _p ≤ 10μs, V _{GE} ≤ 15V V _{CE(max)} = V _{CES} - L* x di/dt IEC 60747-9		480		A

Note:

* L is the circuit inductance + L_M

ELECTRICAL CHARACTERISTICS

T_{case} = 25°C unless stated otherwise

Symbol	Parameter	Test Conditions	Min	Typ.	Max	Units	
t _{d(off)}	Turn-off delay time	I _C = 125A V _{GE} = ±15V V _{CE} = 1800V R _{g(ON)} = 20Ω R _{g(OFF)} = 20Ω C _{GE} = 27nF L _S ~ 150nH		2700		ns	
t _f	Fall time			610		ns	
E _{OFF}	Turn-off energy loss				313		mJ
t _{d(on)}	Turn-on delay time				960		ns
t _r	Rise time				430		ns
E _{ON}	Turn-on energy loss				200		mJ
Q _{rr}	Diode reverse recovery charge	I _F = 125A V _{CE} = 1800V dI _F /dt = 350A/μs		70		μC	
I _{rr}	Diode reverse recovery current			75		A	
E _{rec}	Diode reverse recovery energy			85		mJ	

T_{case} = 125°C unless stated otherwise

Symbol	Parameter	Test Conditions	Min	Typ.	Max	Units	
t _{d(off)}	Turn-off delay time	I _C = 125A V _{GE} = ±15V V _{CE} = 1800V R _{g(ON)} = 20Ω R _{g(OFF)} = 20Ω C _{GE} = 27nF L _S ~ 150nH		2750		ns	
t _f	Fall time			590		ns	
E _{OFF}	Turn-off energy loss				340		mJ
t _{d(on)}	Turn-on delay time				1000		ns
t _r	Rise time				460		ns
E _{ON}	Turn-on energy loss				260		mJ
Q _{rr}	Diode reverse recovery charge	I _F = 125A V _{CE} = 1800V dI _F /dt = 350A/μs		115		μC	
I _{rr}	Diode reverse recovery current			97		A	
E _{rec}	Diode reverse recovery energy			140		mJ	

T_{case} = 150°C unless stated otherwise

Symbol	Parameter	Test Conditions	Min	Typ.	Max	Units	
t _{d(off)}	Turn-off delay time	I _C = 125A V _{GE} = ±15V V _{CE} = 1800V R _{g(ON)} = 20Ω R _{g(OFF)} = 20Ω C _{GE} = 27nF L _S ~ 150nH		2760		ns	
t _f	Fall time			590		ns	
E _{OFF}	Turn-off energy loss				366		mJ
t _{d(on)}	Turn-on delay time				1040		ns
t _r	Rise time				460		ns
E _{ON}	Turn-on energy loss				283		mJ
Q _{rr}	Diode reverse recovery charge	I _F = 125A V _{CE} = 1800V dI _F /dt = 350A/μs		135		μC	
I _{rr}	Diode reverse recovery current			100		A	
E _{rec}	Diode reverse recovery energy			165		mJ	

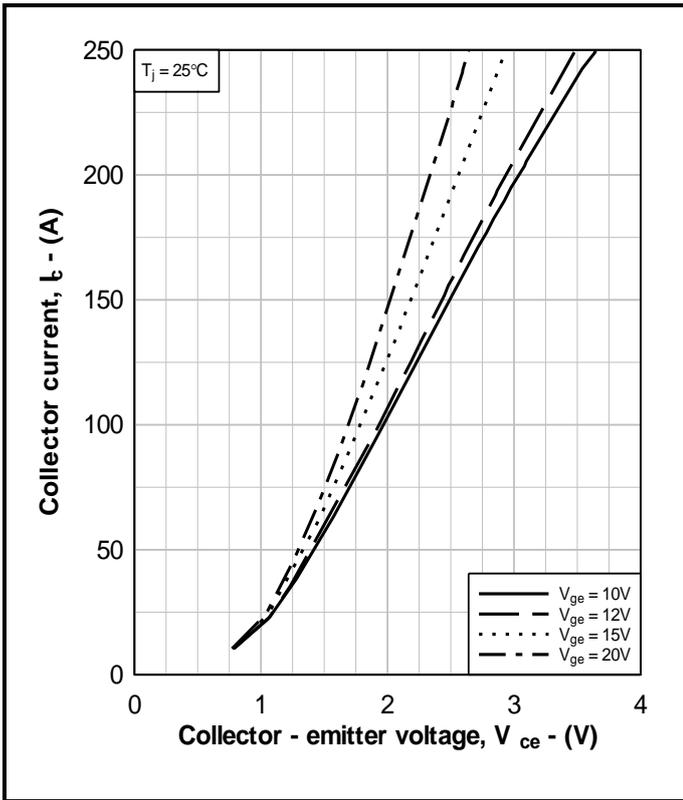


Fig. 3 Typical output characteristics

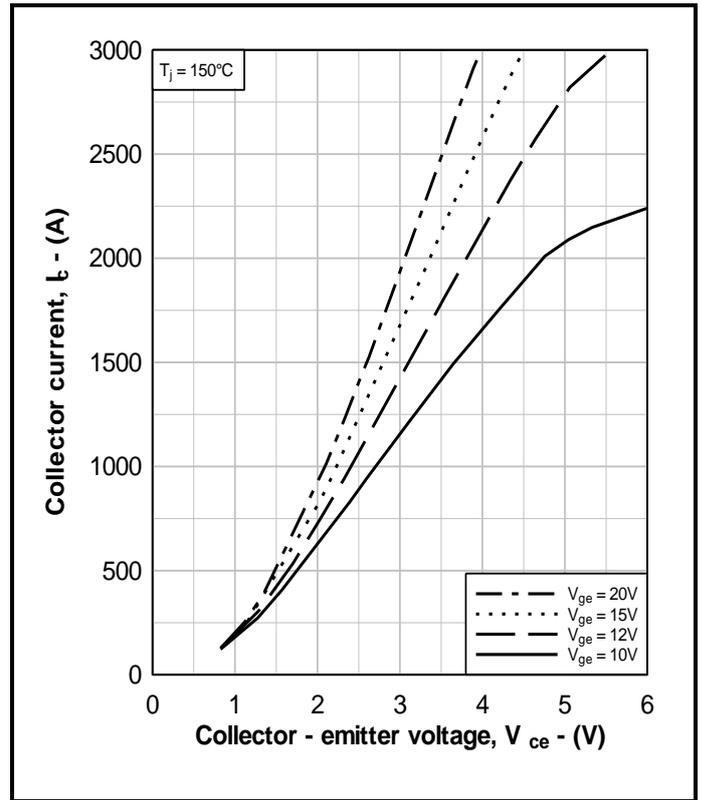


Fig. 4 Typical output characteristics

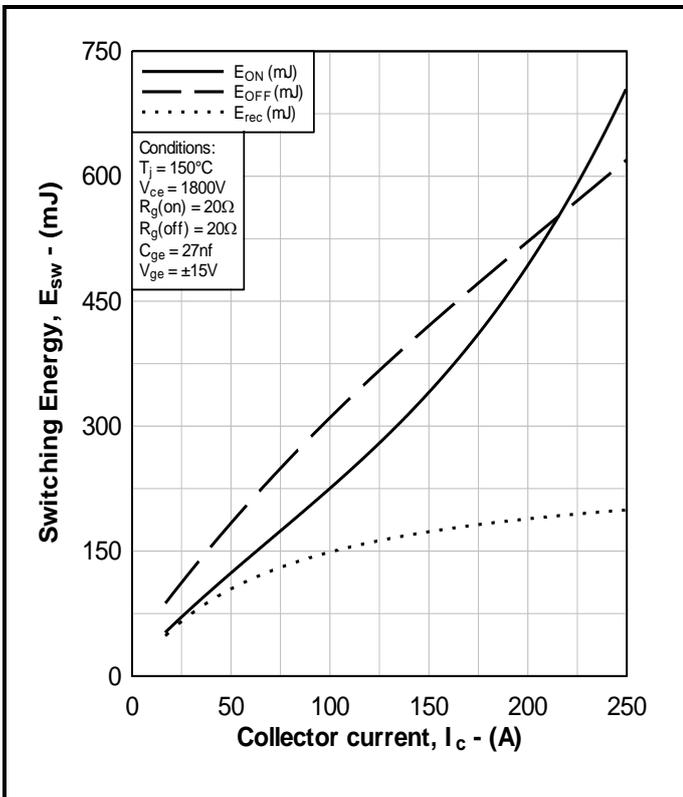


Fig. 5 Typical switching energy vs collector current

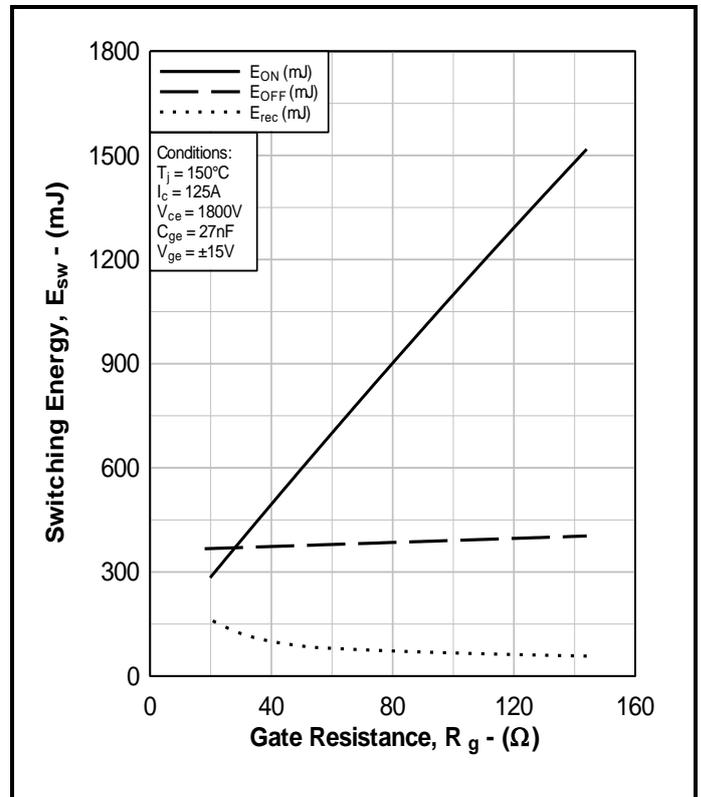


Fig. 6 Typical switching energy vs gate resistance

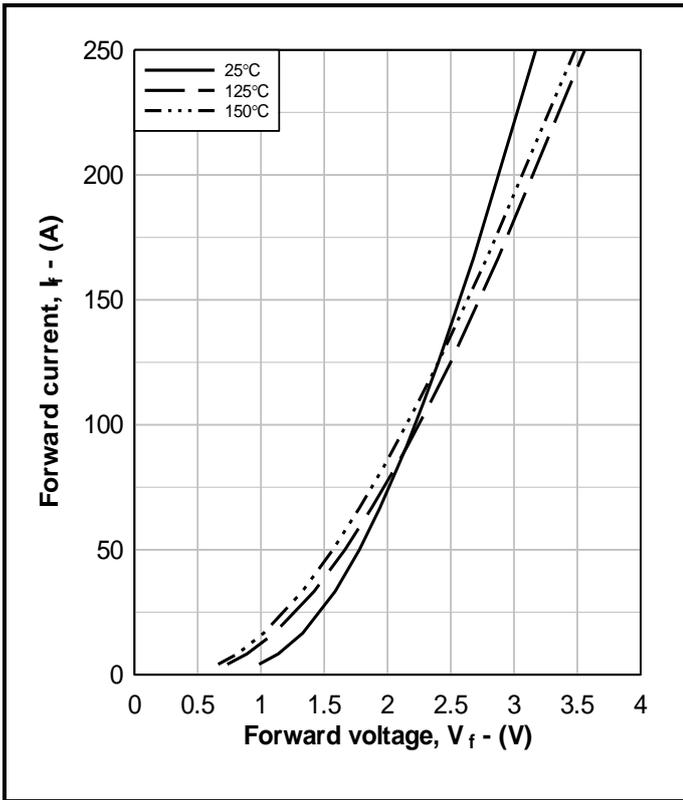


Fig. 7 Diode typical forward characteristics

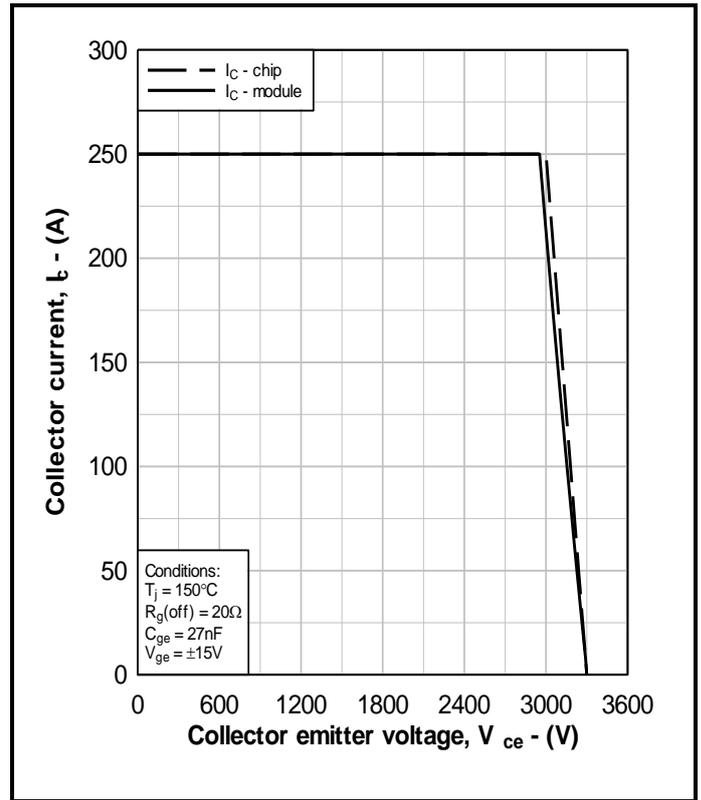


Fig. 8 Reverse bias safe operating area

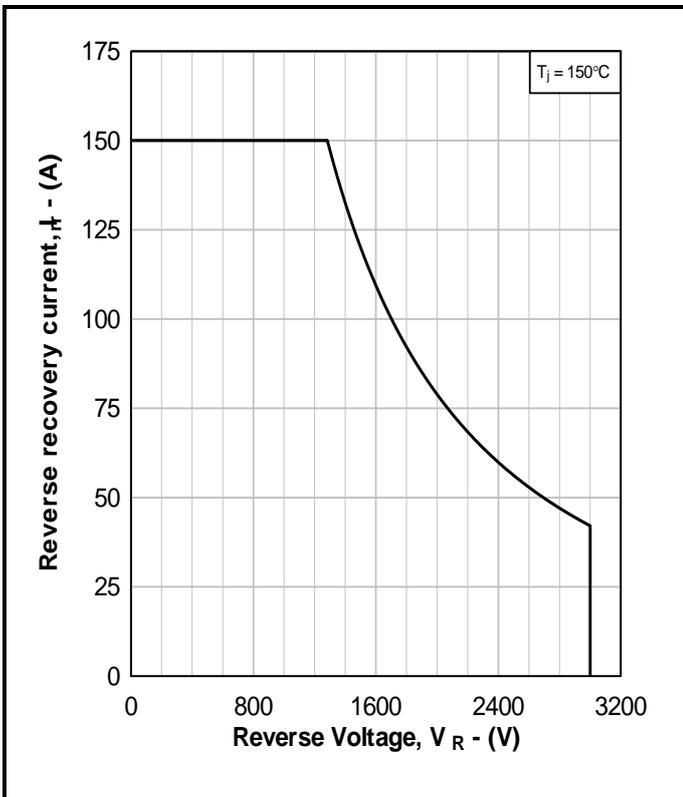


Fig. 9 Diode reverse bias safe operating area

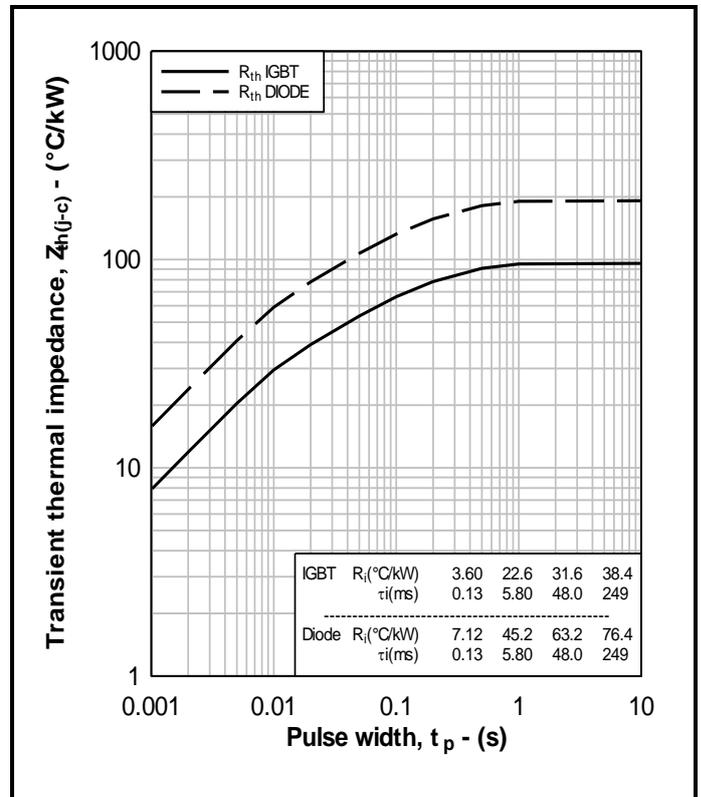


Fig. 10 Transient thermal impedance

PACKAGE DETAILS

For further package information, please visit our website or contact Customer Services.
All dimensions in mm, unless stated otherwise.
DO NOT SCALE.

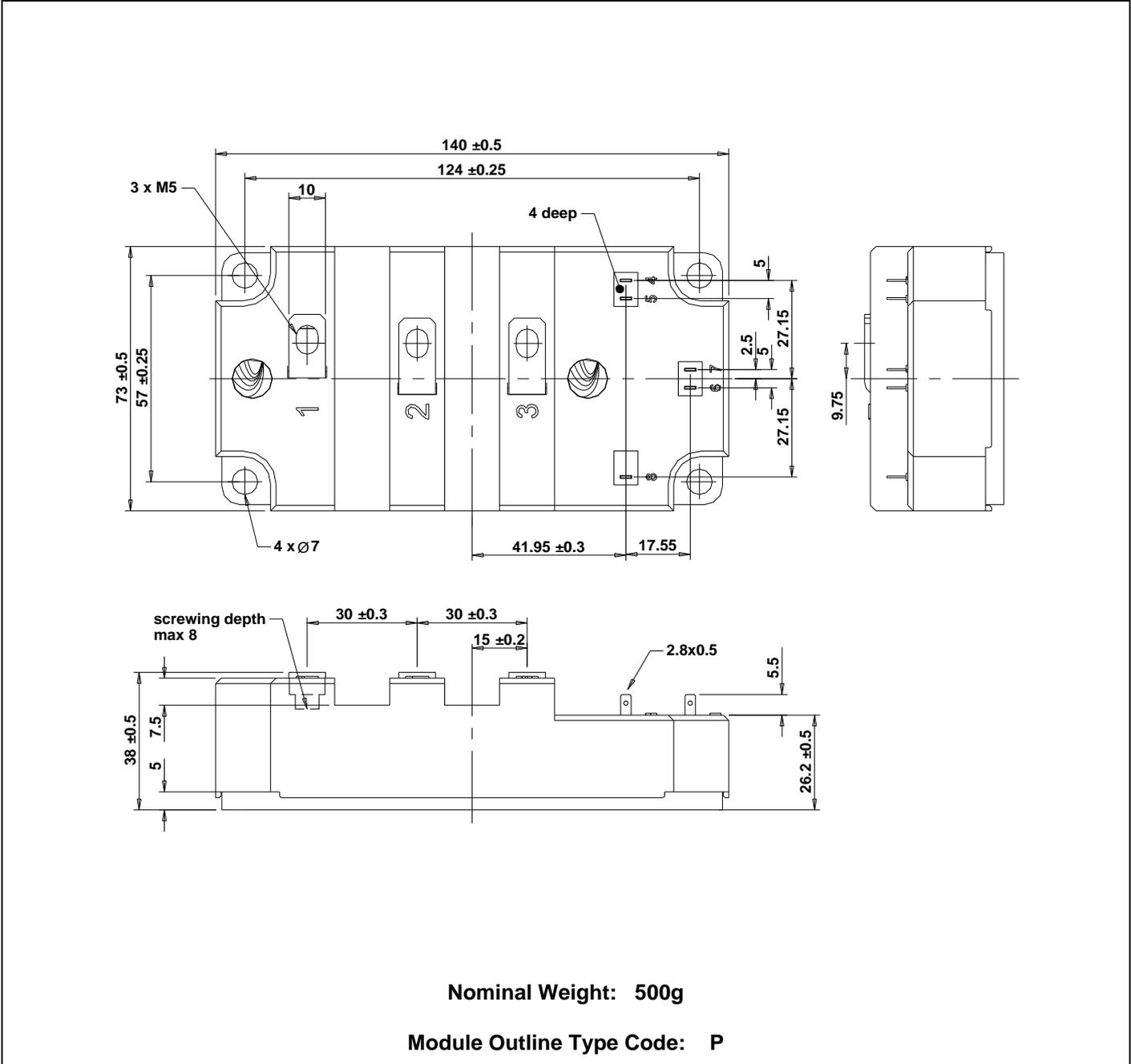


Fig. 11 Module outline drawing

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